

Si Photodiode

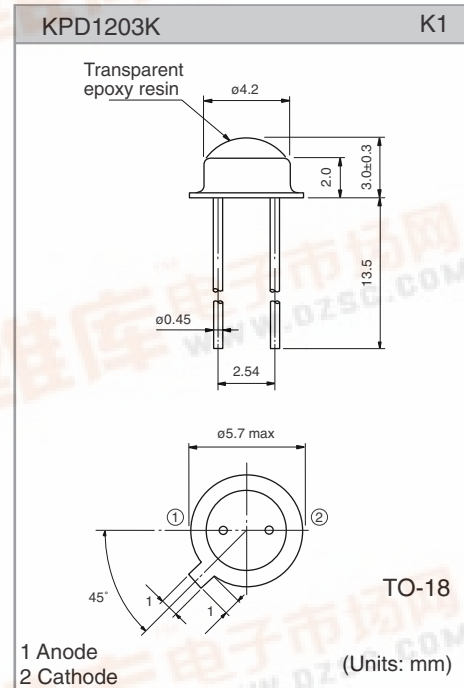
KPD1203K

Features

- Transparent epoxy potting
- High sensitivity
- Broad directivity
- Unbiased for low frequency or biased for high frequency measurement

Applications

- Optical switches
- Optical encoders
- Pulse detectors
- Sensors and industrial controls



Maximum ratings

Item	Symbol	Value	Units
Reverse Voltage	V_R	15	V
Reverse Current	I_R	500	μA
Forward Current	I_F	60	mA
Operating Temperature	T_{op}	-20 ~ +100	°C
Storage Temperature	T_{stg}	-30 ~ +100	°C

Characteristics ($T_a=25^\circ C$ unless otherwise noted.)

Parameter	Symbol	Min.	Typ.	Max.	Units	Test Conditions
Active Dia.	D	0.92x0.92			mm	
Operating Voltage	V_{RO}		0		V	For low frequency
			5			For high frequency
Sensitive Wavelength		450	950(ρ)	1100	nm	ρ =Peak wavelength
Open Circuit Voltage	V_{op}	320	400		mV	1000lux(@2856K)
Short Circuit Current	I_{sh}	4	9		μA	
Dark Current	I_d		0.1	1	nA	$V_R=5V$
Capacitance	C		50	60	pF	$V=0, f=1MHz$
Rise/Fall Time	t_r		8	10	ns	$V_R=5V, \lambda=780nm, R_L=50$
	t_f		27	35		
Cutoff Frequency	f_c	10	15		MHz	$V_R=5V, \lambda=780nm, R_L=50$

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